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M. Brunson

PATENT
0020-4666P

4/23/02

IN THE U.S. PATENT AND TRADEMARK OFFICE

Applicant: Fumihiko KONUSHI et al. Conf.: 1396
Application No.: 09/492,803 Group: 2828
Filed: January 28, 2000 Examiner: Q. Leung
For: SEMICONDUCTOR LASER DEVICE AND METHOD
OF MANUFACTURING SAME

RECEIVED
APR 17 2002
TECHNOLOGY CENTER 2800AMENDMENTAssistant Commissioner for Patents
Washington, DC 20231

April 15, 2002

Sir:

In reply to the Office Action dated January 15, 2002, the following amendments and remarks are respectfully submitted in the above-identified application.

IN THE CLAIMS:

Please amend the claims as follows:

- Subs 7
C1
B1
1. (Twice Amended) A semiconductor laser device having a quantum well active layer disposed between a pair of cladding layers; and an optical guide layer disposed between at least one of the cladding layers and the quantum well active layer, wherein a spacer layer is provided between said optical guide layer and said at least one of the cladding layers, said spacer layer having an interface between the spacer layer and said optical guide layer.

04/16/2002 HABDI1 00000057 09492803

01 FC:102
02 FC:103252.00 OP
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